

AUTOMOTIVE

RoHS

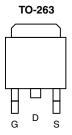
COMPLIANT

HALOGEN

FREE

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

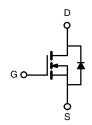
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0041				
I <sub>D</sub> (A)	50				
Configuration	Single				



Top View

#### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified<sup>d</sup>
- 100 %  $\rm R_g$  and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM50N04-4m1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V <sub>DS</sub>	40	N/		
Gate-Source Voltage		V <sub>GS</sub>	± 20	V		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	50			
	T <sub>C</sub> = 125 °C		50			
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	50	А			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	200				
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	60			
Single Pulse Avalanche Energy		E <sub>AS</sub>	180	mJ		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	150	w		
	T <sub>C</sub> = 125 °C		50	vv		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1	0/10	

#### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

S12-0568-Rev. A, 26-Mar-12

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## SQM50N04-4m1



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		40	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.0	3.5	v
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = 40 V, $T_{J}$ = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \geq 5 \ V$	50	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0030	0.0041	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0068	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0082	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		-	200	-	S
Dynamic <sup>b</sup>	<u>.</u>						
Input Capacitance	C <sub>iss</sub>			-	5372	6715	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	512	640	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	256	320	
Total Gate Charge <sup>c</sup>	Qg			-	70	105	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$	-	16	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	12.6	-	
Gate Resistance	Rg		f = 1 MHz		1.86	2.8	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				12	18	
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 20 \ \text{V}, \ R_{\text{L}} = 0.4 \ \Omega \\ \\ I_{\text{D}} \cong 50 \ \text{A}, \ V_{\text{GEN}} = 10 \ \text{V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	5	8	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	35	53	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α
Forward Voltage	V <sub>SD</sub>	$I_{\rm F} = 50 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.86	1.5	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

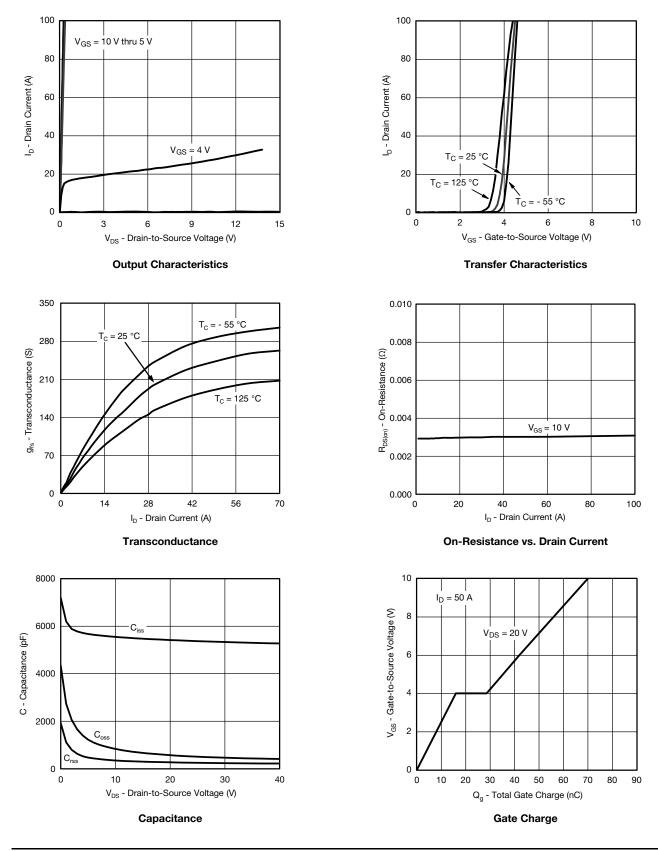
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## SQM50N04-4m1

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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S12-0568-Rev. A, 26-Mar-12

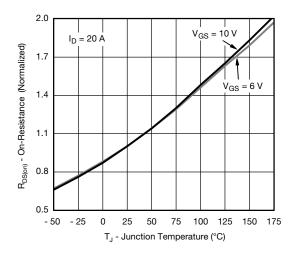
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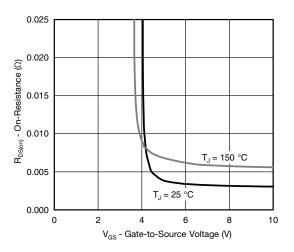




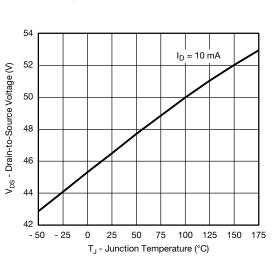
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



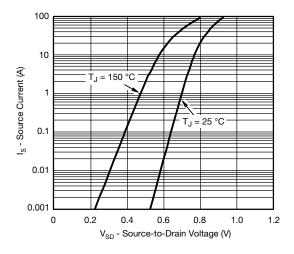
#### **On-Resistance vs. Junction Temperature**



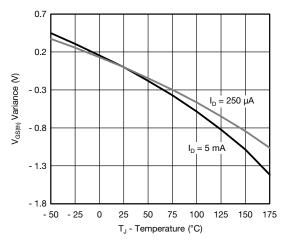
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage





Document Number: 63770

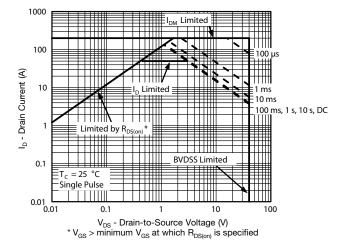
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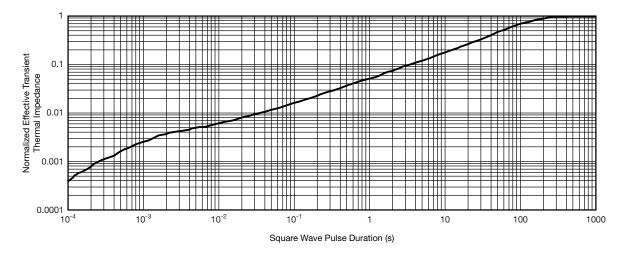
SQM50N04-4m1

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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



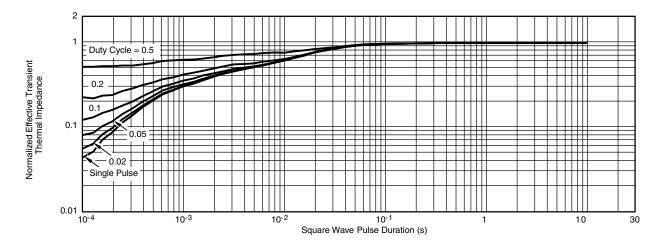
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	К	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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